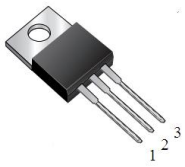
CURRENT 10 Ampere
VOLTAGE RANG 600 Volts

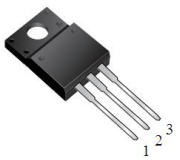
ASE10N60

FEATURE

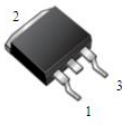
- 10A,600V,$R_{DS(ON)}$=0.85Ω@V_{GS}=10V/5A
- Low gate charge
- Low C_{iss}
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



TO-220AB
10N60

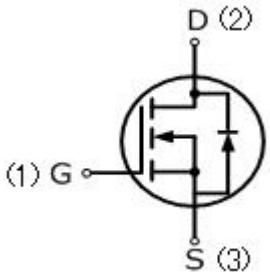


ITO-220AB
10N60F



TO-263
10N60B

TO-262
10N60H



Absolute Maximum Ratings(T_C=25℃,unless otherwise noted)

Parameter		Symbol	ASE10N60	UNIT
Drain-Source Voltage		V_{DSS}	600	V
Gate-Source Voltage		V_{GSS}	±30	
Continuous Drain Current		I_D	10	A
Pulsed Drain Current(Note1)		I_{DM}	40	
Single Pulse Avalanche Energy (Note 2)		E_{AS}	300	mJ
Avalanche Current(Note1)		I_{AR}	10	A
Repetitive Avalanche Energy (Note1)		E_{AR}	30	mJ
Reverse Diode dV/dt (Note 3)		dv/dt	5.5	V/ns
Operating Junction and Storage Temperature Range		T_J,T_{STG}	-55 to +150	℃
Maximum lead temperature for soldering purposes, 1/8″from case for 5 seconds		T_L	260	℃
Mounting Torque	6-32 or M3 screw		10	lbf • in
			1.1	N • m

Thermal Characteristics

Parameter		Symbol	ITO-220	TO-220	TO-262 TO-263	Units
Maximum Junction-to-Case		R_{thJC}	1.0	0.8	0.8	℃/W
Maximum Power Dissipation	T_C=25℃	P_D	125	155	155	W

CURRENT 10 Ampere
VOLTAGE RANG 600 Volts

ASE10N60

Electrical Characteristics (T_c=25℃,unless otherwise noted)

Parameter	Symbol	Test Conditions	Mix	Typ	Max	Units
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V,I_D=250uA	600	—	—	V
Breakdown Temperature Coefficient	ΔBV_{DSS} /ΔT_J	Reference to 25℃, I_D=250uA	—	0.6	—	V/℃
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=600V,V_{GS}=0V	—	—	1	uA
Gate-Body Leakage Current,Forward	I_{GSSF}	V_{GS}=30V,V_{DS}=0V	—	—	10	uA
Gate-Body Leakage Current,Reverse	I_{GSSR}	V_{GS}=-30V,V_{DS}=0V	—	—	-10	uA
On Characteristics						
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS}=10,I_D=250uA	2	—	4	V
Drain-Source On-State Resistance	$R_{DS(on)}$	V_{GS}=10V,I_D=5A	—	—	0.85	Ω
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{DS}=25V,V_{GS}=0V, f=1.0MHZ	—	—	1500	pF
Output Capacitance	C_{oss}		—	—	180	pF
Reverse Transfer Capacitance	C_{rss}		—	—	15	pF
Switching Characteristics						
Turn-On Delay Time	$t_{d(on)}$	V_{DD}=300V,I_D=10A, R_G=25Ω (Note4,5)	—	20	—	ns
Turn-On Rise Time	t_r		—	20	—	ns
Turn-Off Delay Time	$t_{d(off)}$		—	55	—	ns
Turn-Off Fall Time	t_f		—	30	—	ns
Total Gate Charge	Qg	V_{DS}=480V,I_D=10A, V_{GS}=10V, (Note4,5)	—	60	—	nC
Gate-Source Charge	Qgs		—	12	—	nC
Gate-Drain Charge	Qgd		—	28	—	nC
Drain-Source Body Diode Charcteristics and Maximum Ratings						
Continuous Diode Forward Current	I_S		—	—	10	A
Pulsed Diode Forward Current	I_{SM}		—	—	40	A
Diode Forward Voltage	V_{SD}	I_S=10A,V_{GS}=0V	—	—	1.5	V
Reverse Recovery Time	t_{rr}	V_{GS}=0V,I_S=10A, dI_F/dt=100A/us, (Note4)	—	600	—	ns
Reverse Recovery Charge	Q_{rr}		—	4.3	—	uC